

I hereby claim the benefit under Title 35, United States Code, § 120/365 of any United States and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Please address all correspondence to Thomas J. D'Amico of **Dickstein Shapiro Morin & Oshinsky LLP** located at 2101 L Street NW, Washington, DC 20037-1526. Telephone calls should be made to (202) 785-9700.

Full name of first inventor: Kevin M. Devereaux

Inventor's signature: Kevin M. Devereaux Date: 8/24/01

Residence: Boise, Idaho

Citizenship:

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DECLARATION FOR PATENT APPLICATION

My residence, post office address and citizenship are as stated below next to my name.

METHOD AND APPARATUS FOR WAFER LEVEL TESTING OF SEMICONDUCTOR USING SACRIFICIAL ON DIE POWER AND GROUND METALIZATION

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by an amendment, if any, specifically referred to in this oath or declaration.

I hereby claim foreign priority benefits under Title 35, United States Code § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Priority
Not
Claimed

1

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11

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